

BiTS China 2016

Premium Archive

2nd Annual



September 13, 2016

Session 2

© 2016 BiTS Workshop – Image: 一花一菩提/HuiTu.com

Presentation / Copyright Notice

The presentations in this publication comprise the pre-workshop Proceedings of the BiTS China Workshop. They reflect the authors' opinions and are reproduced here as they are planned to be presented at the BiTS China Workshop. Updates from this version of the papers may occur in the version that is actually presented at the BiTS China Workshop. The inclusion of the papers in this publication does not constitute an endorsement by the BiTS Workshop or the sponsors.

There is NO copyright protection claimed by this publication. However, each presentation is the work of the authors and their respective companies: as such, it is strongly encouraged that any use reflect proper acknowledgement to the appropriate source. Any questions regarding the use of any materials presented should be directed to the author/s or their companies.

The BiTS logo, 'Burn-in & Test Strategies Workshop', 'BiTS China', and 'Burn-in & Test Strategies China Workshop' are trademarks of BiTS Workshop.

Session 2

Frank Zhou
Session Chair

BiTS China

Socket Technology

"Study of Probe Pin Internal Resistance"

Takuto Yoshida - Test Tooling Solutions Group

"Monte Carlo Analysis for PoP Alignment"

DeXian (Frank) Liu - Smiths Connectors

"Conductive Elastomer vs Spring Probe: Performance & Application"

Jiachun (Frank) Zhou - Smiths Connectors

"Do Socket and Kits Design Matter for Die Cracking?"

Yuanjun Shi - TwinSolution Technology

Session 2

周家春

Session Chair

BiTS China

Socket Technology

"[弹簧探针内部阻值的研究](#)"

Takuto Yoshida - Test Tooling Solutions Group

"[叠层封装测试插座设计中校直的蒙特卡洛分析法](#)"

刘德先 — Smiths Connectors

"[导电胶与弹簧探针技术的比较以及在半导体测试领域的性能与应用](#)"

周家春 (Frank) 博士, 刘德先 — Smiths Connectors

"[测试插座和快速切换治具的设计对芯片碎片的影响](#)"

施元军, 上海韬盛电子科技股份有限公司

BiTS China 2016

Study of Probe Pin Internal Resistance

Takuto Yoshida
Test Tooling Solutions Group



BiTS China Workshop
Suzhou
September 13, 2016



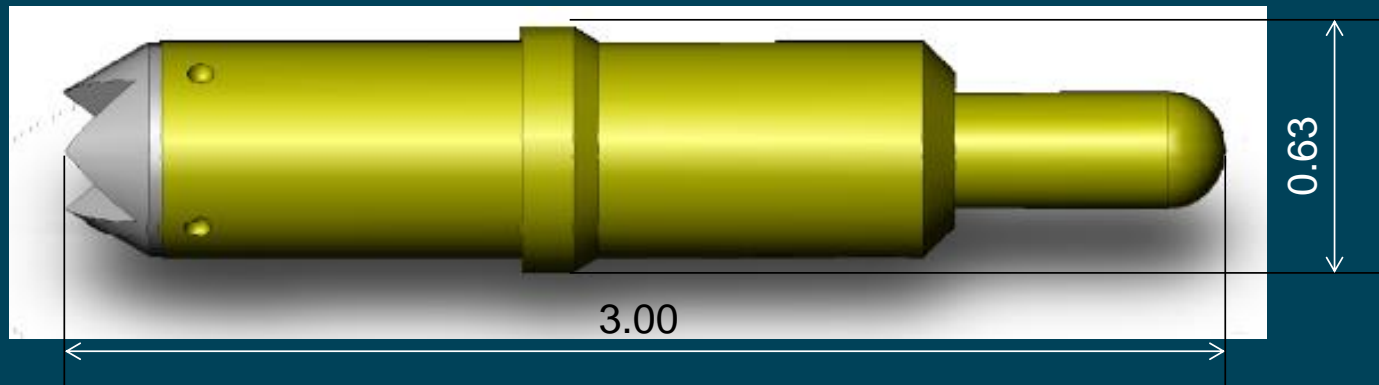
BiTS China 2016

Contents

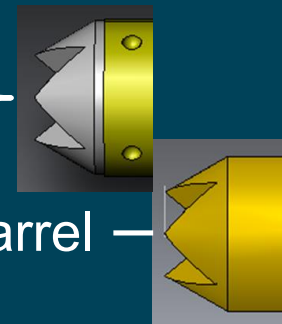
- CRES Comparison by Pin Design
- CRES Composition in a Probe Pin
- Material Resistance
- Contact Resistance
- Individual CRES Measurement
- Conclusion

BiTS China 2016

CRES Comparison by Pin Design



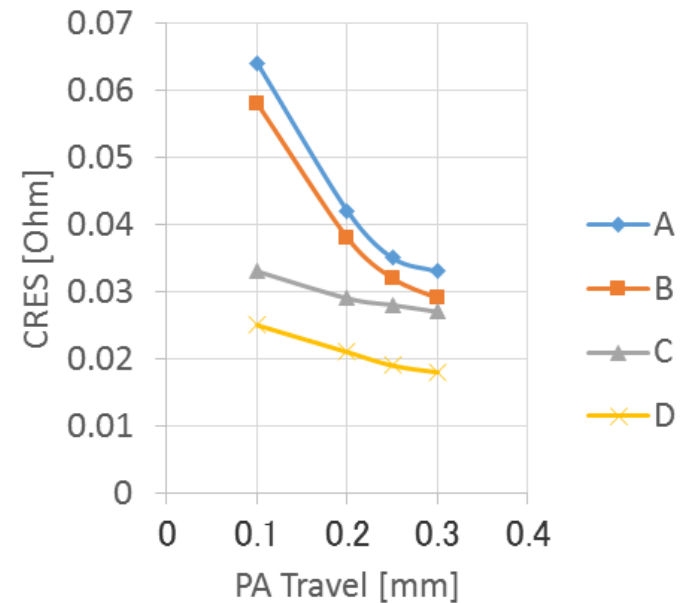
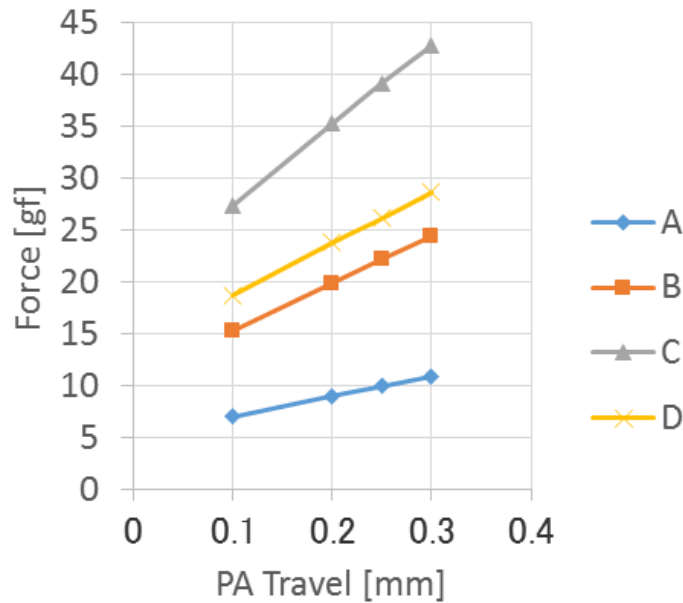
- Pin Pitch: 0.8mm
- Test Height: 2.5mm
- Pin Design
 - “A”: 10gf, 4-point crimped PA
 - “B”: 25gf, 4-point crimped PA
 - “C”: 42gf, 4-point crimped PA
 - “D”: 28gf, Combined PA and Barrel



PA: Plunger A (device side)

BiTS China 2016

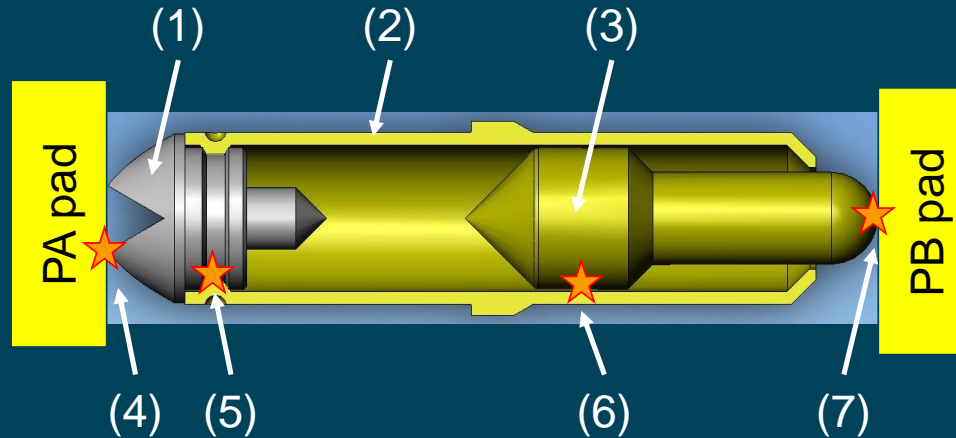
CRES Comparison by Pin Design



- Higher pin force is lower CRES pin
- Combined PA and Barrel pin (“D”) is the lowest CRES pin
- CRES differ by pin design (18 mOhm to 33 mOhm)

BiTS China 2016

CRES Composition in a Probe Pin



Note

PA: Plunger A (device side)

PB: Plunger B (PCB side)

BR: Barrel

Spring is removed from the drawing because it is no contribution to CRES path

- (1) PA material electrical resistance
- (2) BR material electrical resistance
- (3) PB material electrical resistance
- (4) PA pad to PA contact resistance
- (5) PA to BR contact resistance
- (6) BR to PB contact resistance
- (7) PB to PB pad contact resistance

Material resistance

Contact resistance

BiTS China 2016

Material Resistance

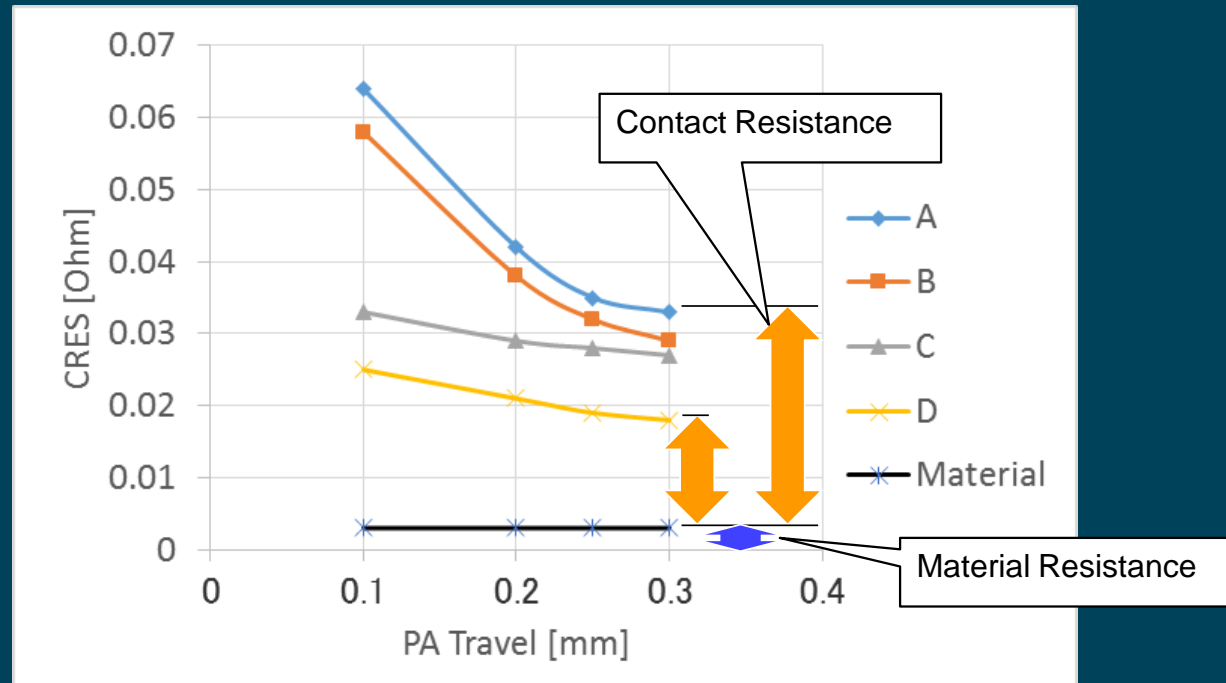
$$R = \rho \frac{L}{A}$$

- R: Electrical resistance (measured in ohms, Ω)
- ρ : Electrical resistivity (measured in ohm·meters, $\Omega \cdot \text{m}$)
- L: Length of material (measured in meters, m)
- A: Cross-sectional area of material (measured in square meters, m^2)

Total Material Resistance  R = 0.003 Ohm

BiTS China 2016

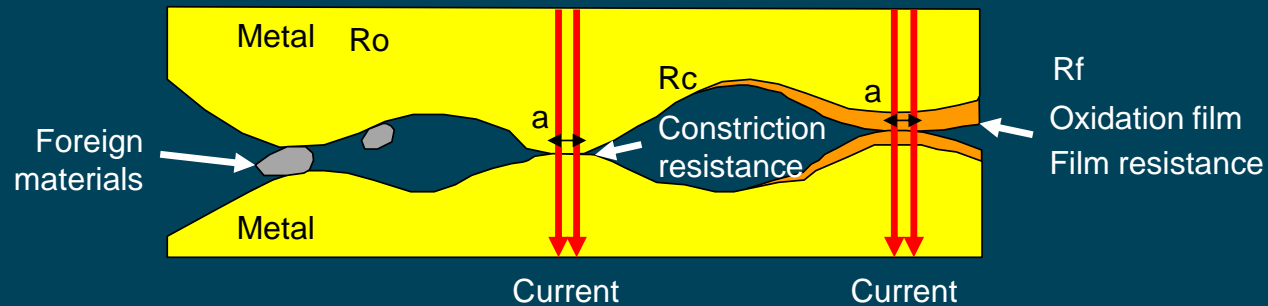
Material Resistance Contribution



- Material resistance contribution is only 9% to 17%
- Contact resistance is main player for pin CRES

BiTS China 2016

Contact Resistance

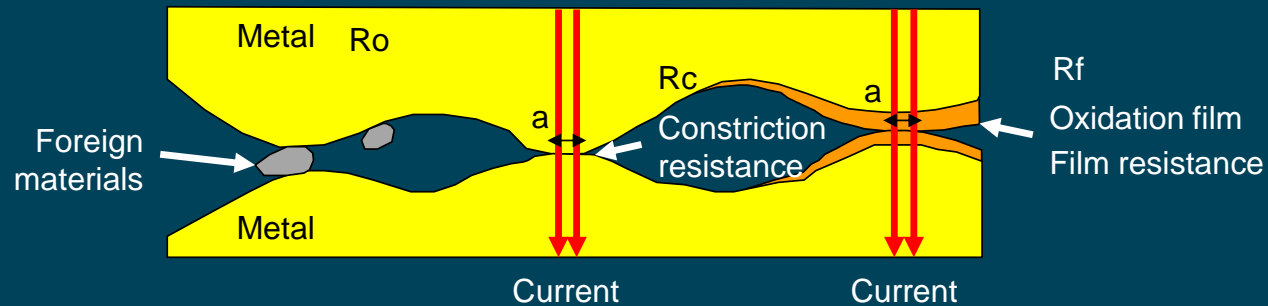


$$R = R_c + R_f + R_o$$

- R : Electrical resistance (measured in ohms, Ω)
- R_c : Constriction resistance (measured in ohms, Ω)
- R_f : Film resistance (measured in ohms, Ω)
- R_o : Metal specific resistance (measured in ohms, Ω)

BiTS China 2016

Contact Resistance



$$R_c = \frac{\rho}{2a} \quad R_f = \frac{\sigma d}{\pi a^2}$$

- ρ : Electrical resistivity (measured in ohm-meters, $\Omega \cdot m$)
- a : True contact area diameter (measured in meters, m)
- σ : Film electrical resistivity (measured in ohm-meters, $\Omega \cdot m$)
- d : Film thickness (measured in meters, m)

BiTS China 2016

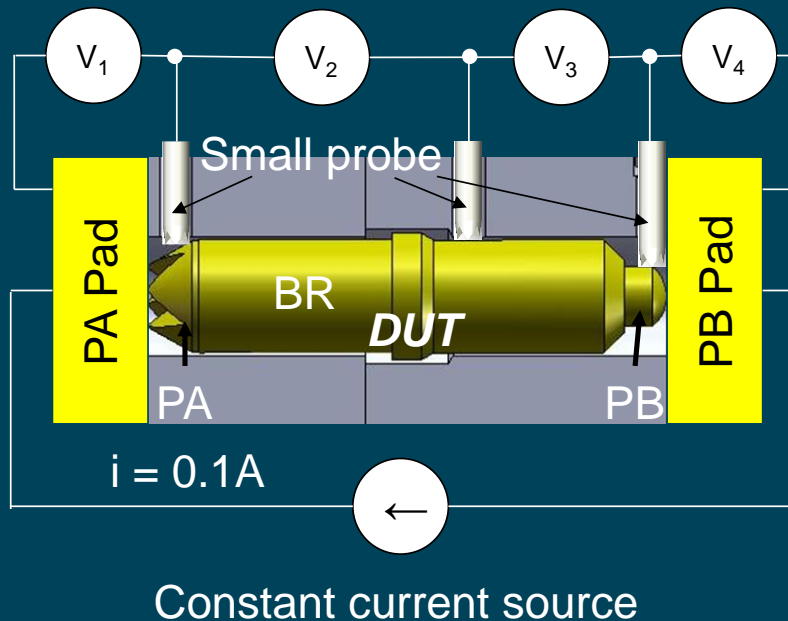
Contact Resistance

- Constriction resistance contributor
 - Contact area shape
 - Contact force
 - Plating material and thickness
 - Hardness
 - Surface roughness
- Film resistance contributor
 - Material
 - Thickness

BiTS China 2016

Individual CRES Measurement

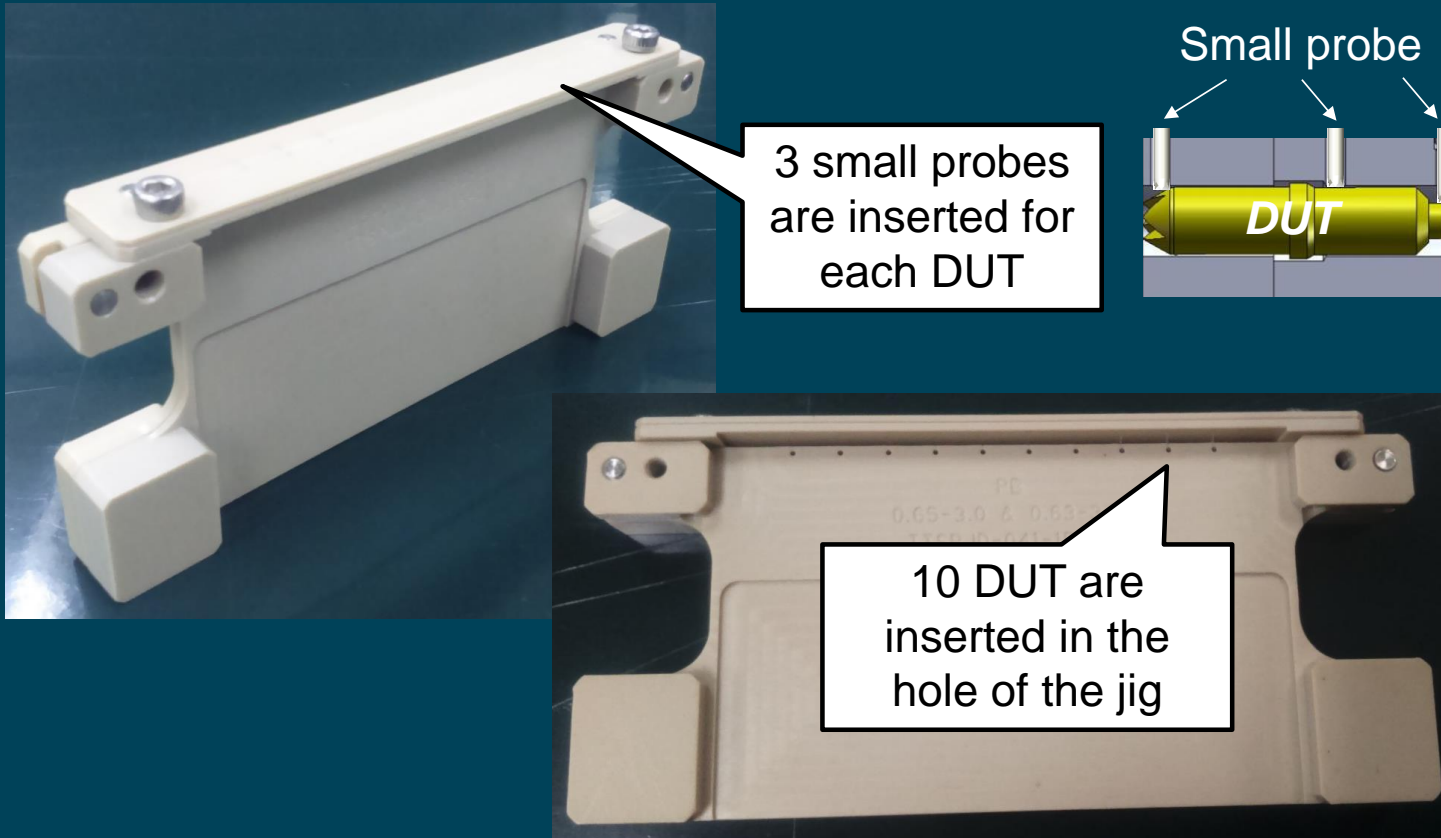
4-wire measurement method



- Source Meter
Keithley 2400
- Digital Multimeter
Yokogawa 7555
- PA Pad and PB Pad
compress DUT
- 3 small probes to contact
DUT surface
- $R_{(PA\ Pad-PA)} = V_1/0.1$
- $R_{(PA-BR)} = V_2/0.1$
- $R_{(BR-PB)} = V_3/0.1$
- $R_{(PB-PB\ Pad)} = V_4/0.1$

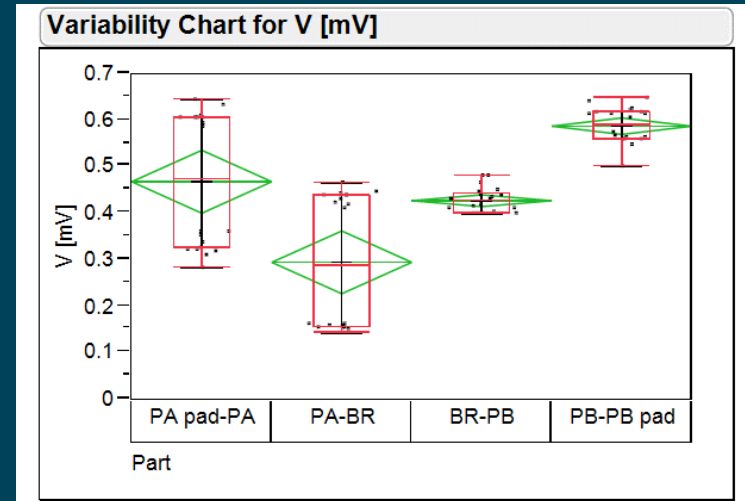
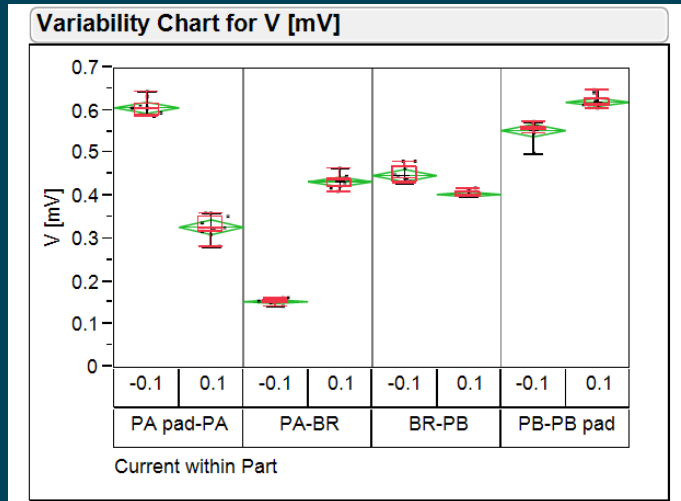
BiTS China 2016

Individual CRES Measurement Jig



BiTS China 2016

Individual CRES Measurement

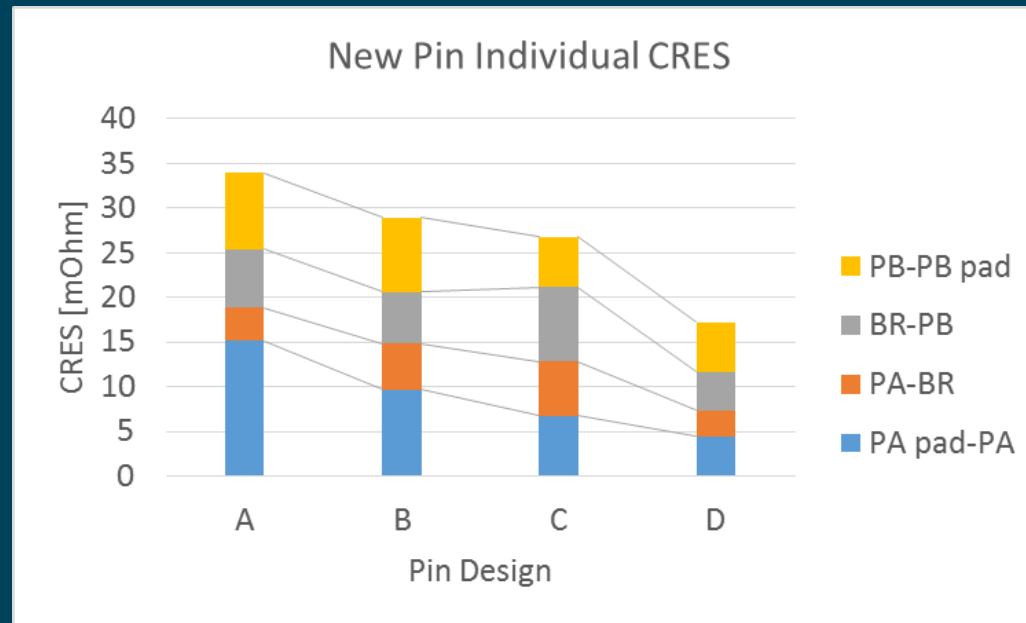


Measurement example

- Measure 10 times for each session with current of +0.1A and -0.1A by considering thermoelectric effect
- Measured voltage was different by thermoelectric effect
- Average voltage value for resistance calculation

BiTS China 2016

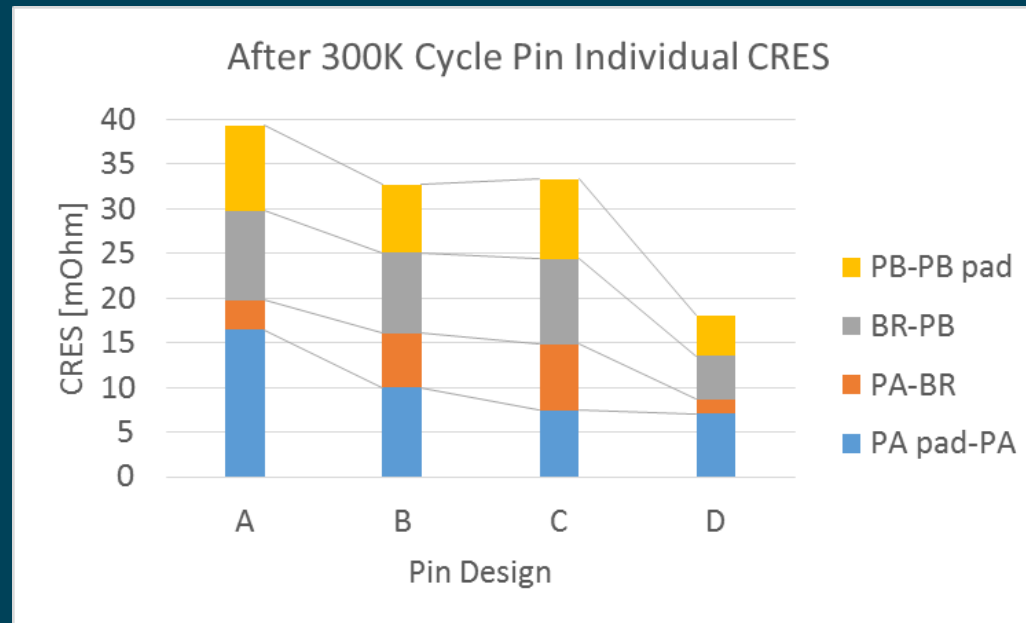
New Pin Individual CRES



- Pin Design “A” (10gf), “B” (25gf), “C” (42gf), “D” Combined PA and BR
- Spring force is most to contact resistance of PA pad – PA, secondary for PB – PB pad
- Combined PA and BR design for “D” design improve contact resistance of PA – BR

BiTS China 2016

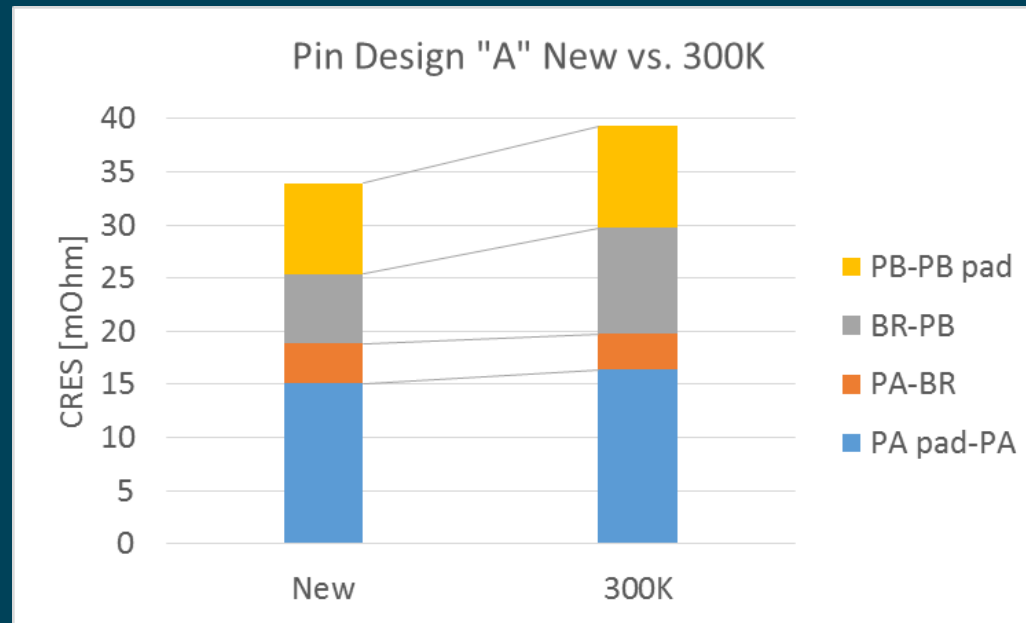
After 300K Cycle Individual CRES



- Pin Design “A” (10gf), “B” (25gf), “C” (42gf), “D” (28gf) Combined PA and Barrel
- Cycle effect mainly impact to contact resistance of BR – PB
- Secondary impact to contact resistance of PB – PB pad

BiTS China 2016

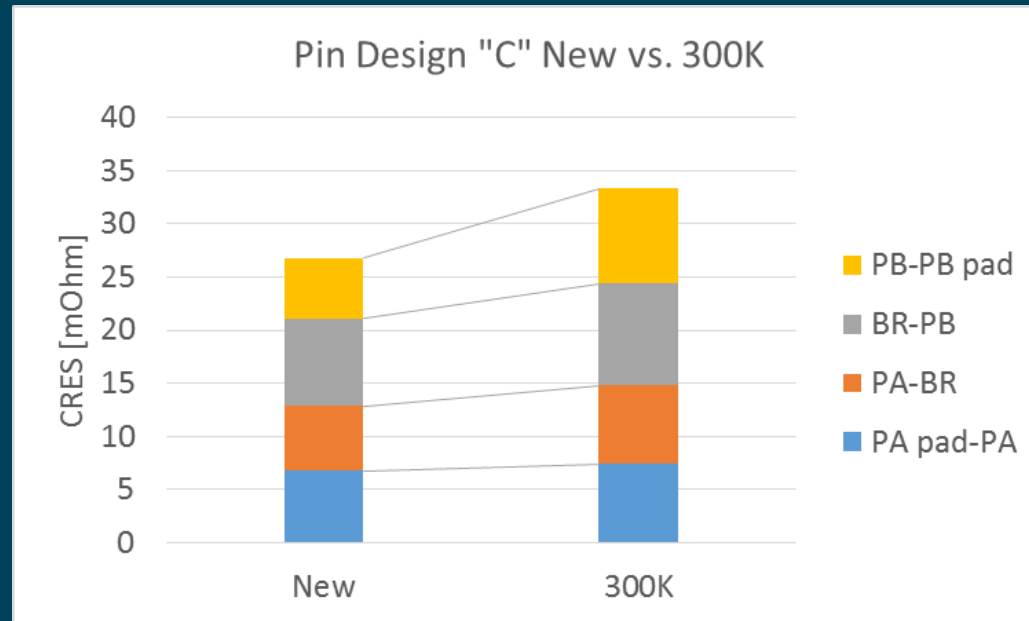
Pin Design "A" New vs. 300K



- 300K cycle test effect mainly impact to contact resistance of BR – PB
- Secondary impact to contact resistance of PA pad – PA

BiTS China 2016

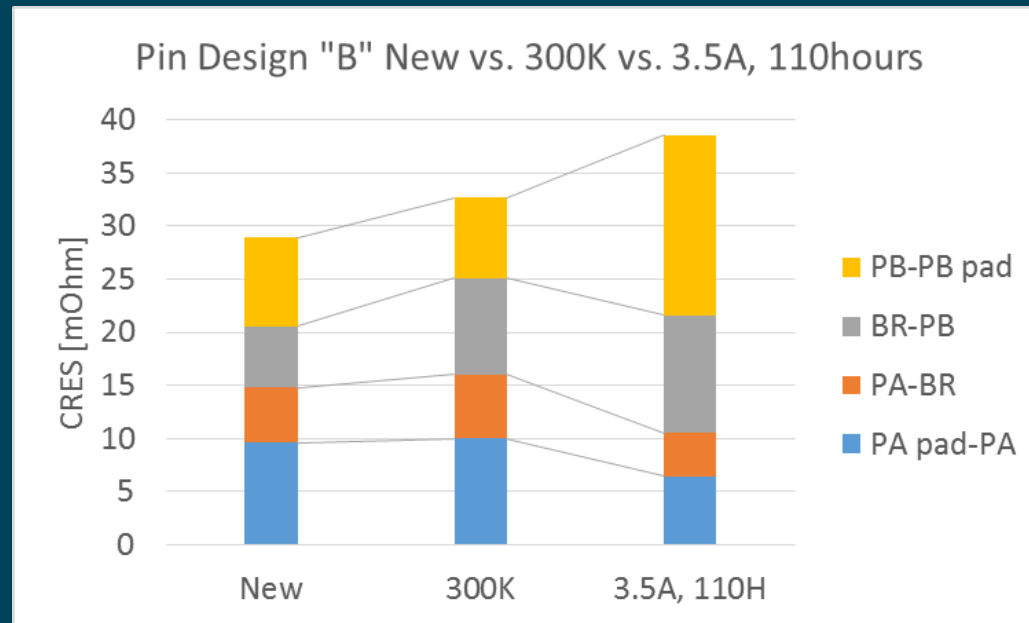
Pin Design "C" New vs. 300K



- 300K cycle test effect mainly impact to contact resistance of PB – PB pad
- Secondary impact to contact resistance of PA – BR

BiTS China 2016

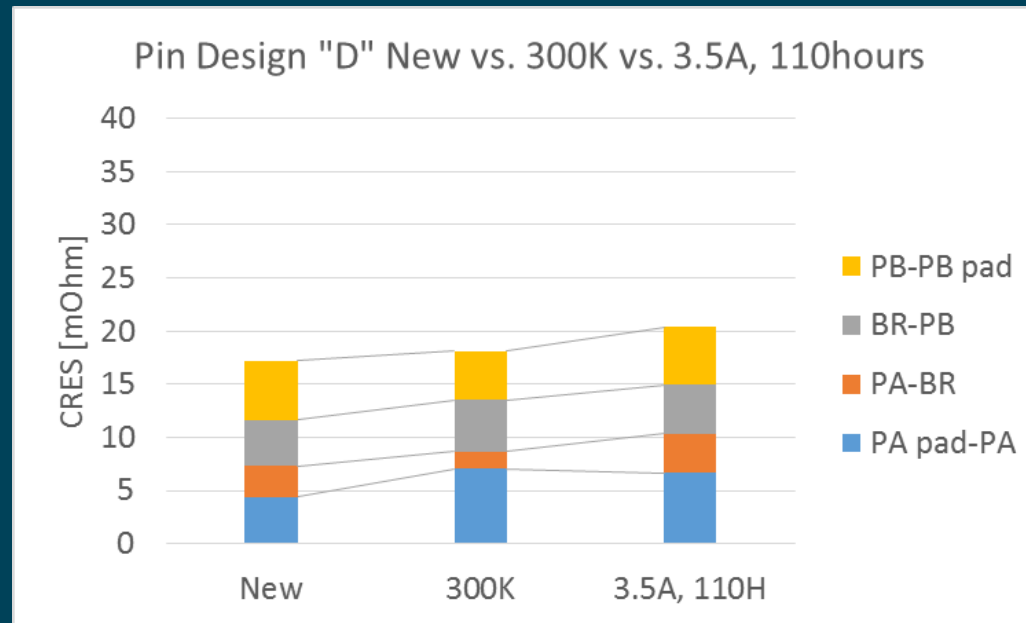
Pin Design "B" New vs. 300K vs. 3.5A 110hours



- Current effect mainly impact to contact resistance of PB – PB pad
- Secondary impact to contact resistance of BR – PB

BiTS China 2016

Pin Design "D" New vs. 300K vs. 3.5A 110hours



- Current effect is smaller than Pin Design "B"
- Low temperature rise by current seems good for pin stability (Low CRES provide low heat (temperature rise))

BiTS China 2016

Conclusion

- Understand CRES Composition in a Probe Pin
- Probe Pin CRES main player is contact resistance
- We can measure each contact resistance by using 4-wire measurement method
- Higher pin force effective to reduce contact resistance of PA pad – PA
- 300K cycle test impact to contact resistance of BR – PB (BR internal surface roughness and PB base shape seems big change)
- 3.5A 110hours test impact to contact resistance of PB – PB pad
- We feedback the probe pin design by result of individual CRES data